

# NTST30100CTG, NTSB30100CT-1G, NTSJ30100CTG, NTSB30100CTG



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## Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low  $V_F = 0.455\text{ V}$  at  $I_F = 5\text{ A}$

### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These are Pb-Free Devices

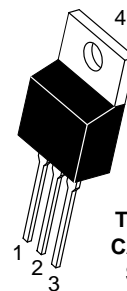
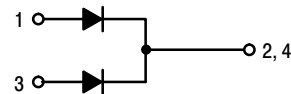
### Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

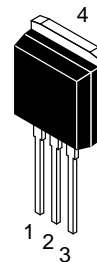
### Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

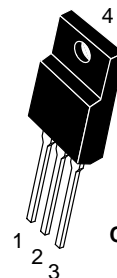
### PIN CONNECTIONS



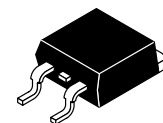
TO-220AB  
CASE 221A  
STYLE 6



I2PAK  
CASE 418D  
STYLE 3



TO-220FP  
CASE 221AH



D2PAK  
CASE 418B

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

# NTST30100CTG, NTSB30100CT-1G, NTSJ30100CTG, NTSB30100CTG

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	100	V
Average Rectified Forward Current (Rated $V_R$ , $T_C = 115^\circ\text{C}$ )	$I_{F(AV)}$ Per device Per diode	30 15	A
Peak Repetitive Forward Current (Rated $V_R$ , Square Wave, 20 kHz, $T_C = 110^\circ\text{C}$ )	$I_{FRM}$ Per device Per diode	60 30	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	$I_{FSM}$	160	A
Operating Junction Temperature	$T_J$	-40 to +150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to +150	$^\circ\text{C}$
Voltage Rate of Change (Rated $V_R$ )	dv/dt	10,000	V/ $\mu\text{s}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Rating	Symbol	NTST30100CTG, NTSB30100CT-1G	NTSB30100CTG	NTSJ30100CTG	Unit
Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.5 70	1.14 46.6	4.09 105	$^\circ\text{C/W}$ $^\circ\text{C/W}$

## ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1) ( $I_F = 5\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $I_F = 7.5\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $I_F = 15\text{ A}$ , $T_J = 25^\circ\text{C}$ )  ( $I_F = 5\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $I_F = 7.5\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $I_F = 15\text{ A}$ , $T_J = 125^\circ\text{C}$ )	$V_F$	0.516 0.576 0.734  0.455 0.522 0.627	- - 0.85  - - 0.68	V
Maximum Instantaneous Reverse Current (Note 1) ( $V_R = 70\text{ V}$ , $T_J = 25^\circ\text{C}$ ) ( $V_R = 70\text{ V}$ , $T_J = 125^\circ\text{C}$ )  (Rated dc Voltage, $T_J = 25^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 125^\circ\text{C}$ )	$I_R$	7.2 8.0  65 20	   500 35	$\mu\text{A}$ mA  $\mu\text{A}$ mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

TYPICAL CHARACTERISTICS

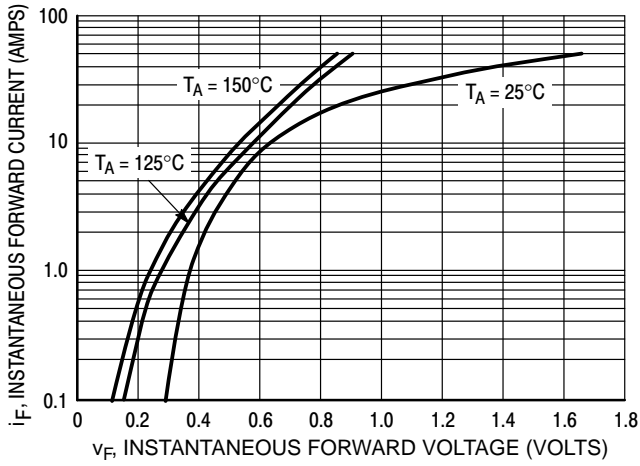


Figure 1. Typical Forward Voltage

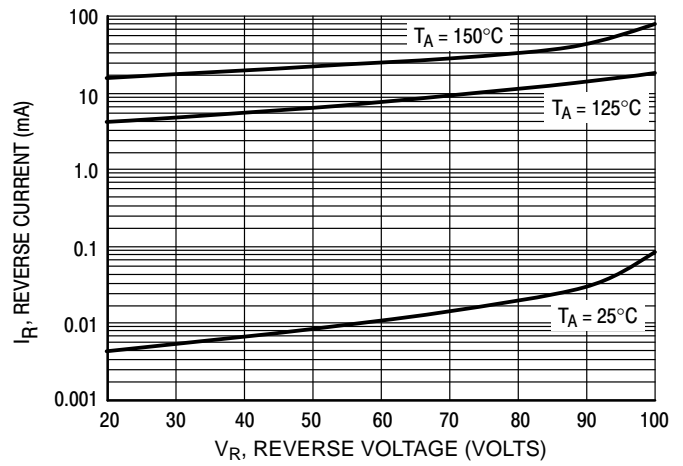


Figure 2. Typical Reverse Current

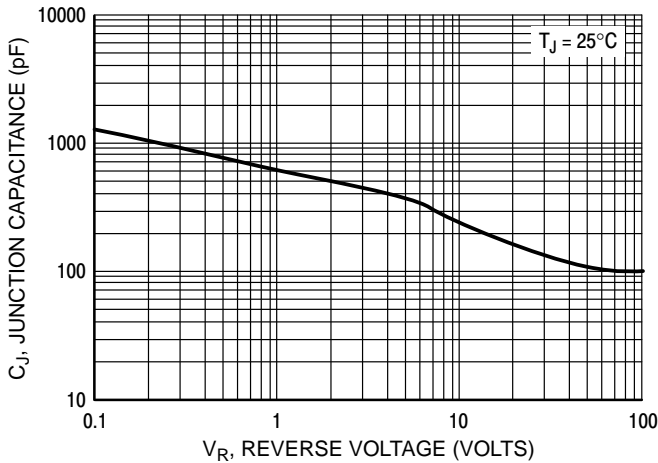


Figure 3. Typical Junction Capacitance

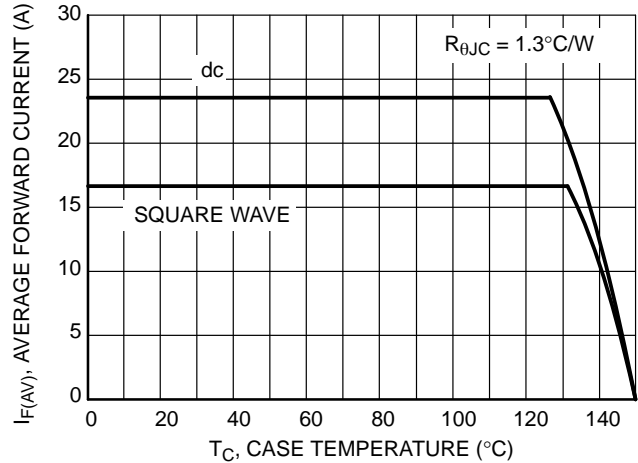


Figure 4. Current Derating per Leg

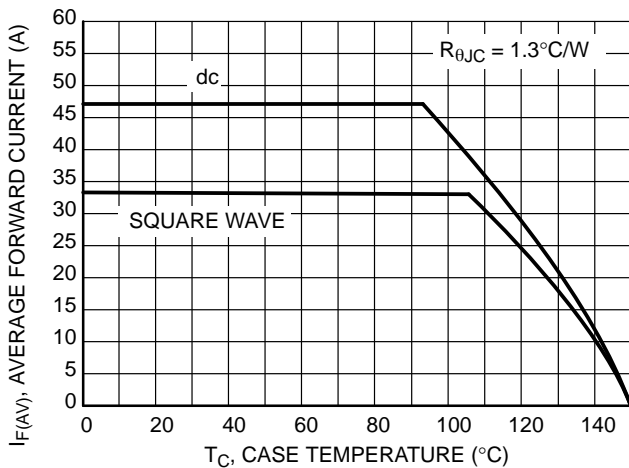


Figure 5. Current Derating

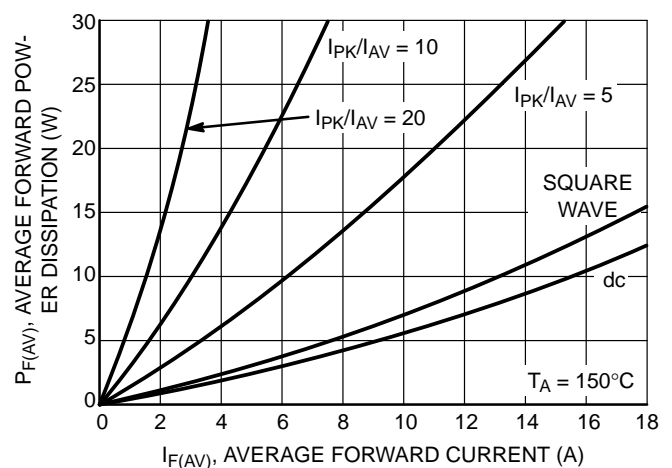


Figure 6. Forward Power Dissipation

TYPICAL CHARACTERISTICS

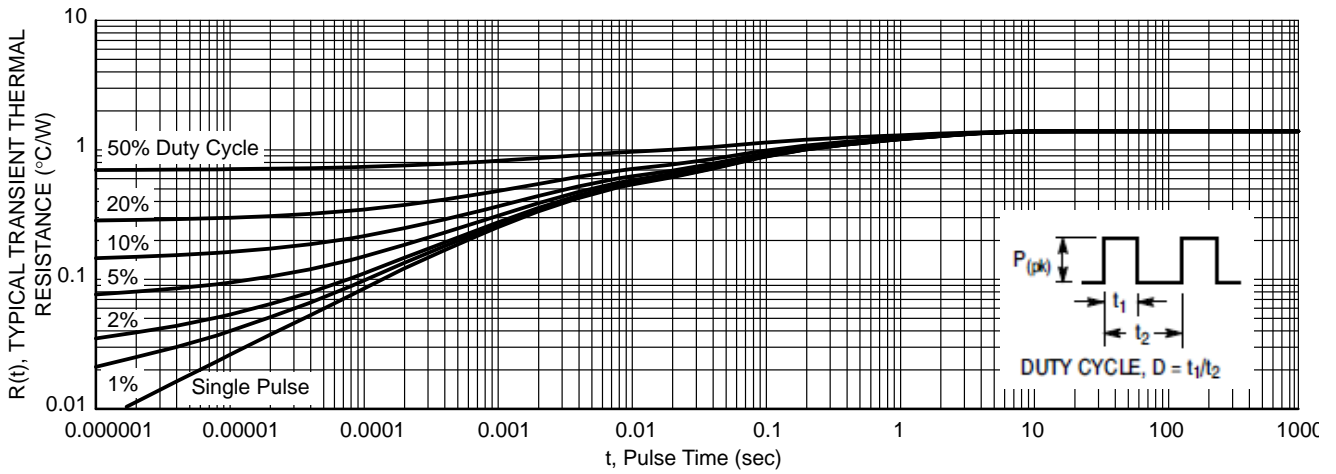


Figure 7. Typical Transient Thermal Response, Junction-to-Case for NTST30100CT and NTSB30100CT-1G

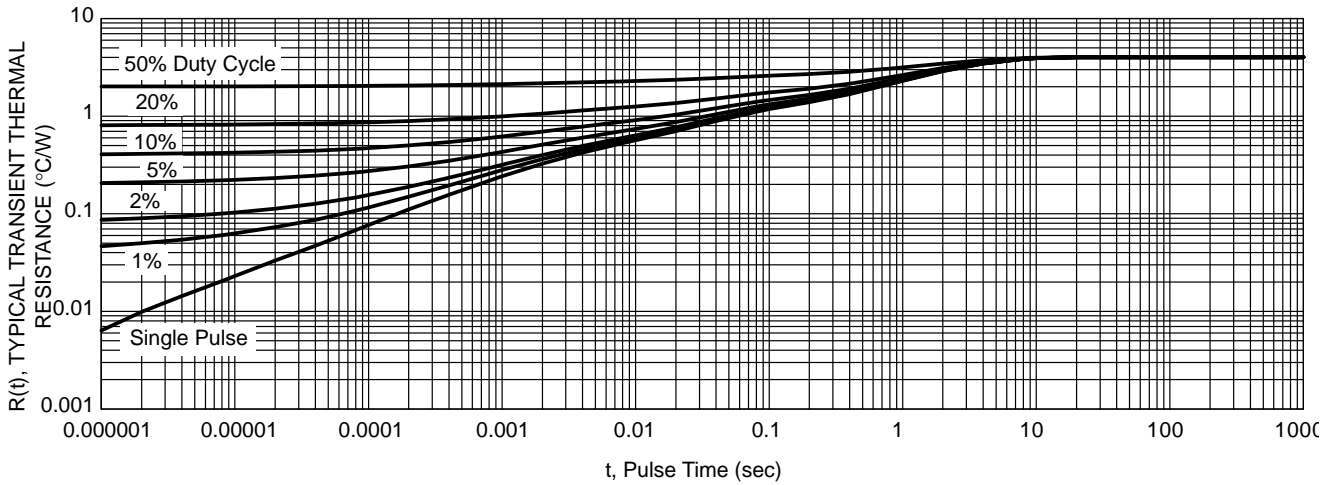


Figure 8. Typical Transient Thermal Response, Junction-to-Case for NTSJ30100CTG

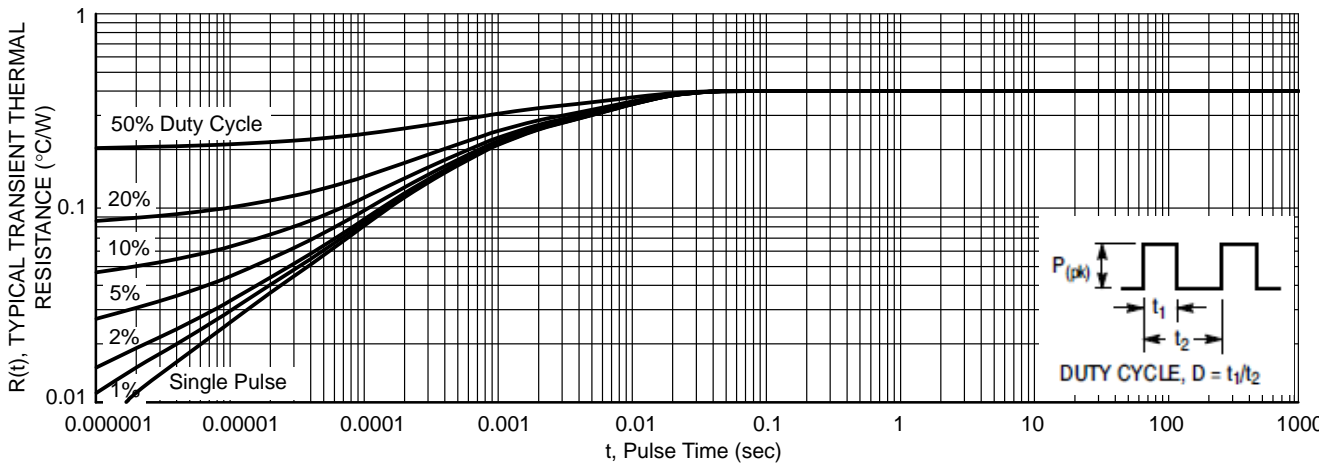


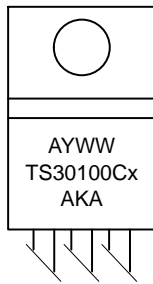
Figure 9. Typical Transient Thermal Response, Junction-to-Case for NTSB30100CTG

# NTST30100CTG, NTSB30100CT-1G, NTSJ30100CTG, NTSB30100CTG

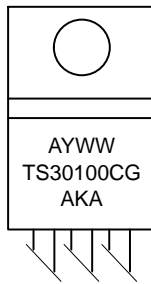
## ORDERING INFORMATION

Device	Package	Shipping
NTST30100CTG	TO-220AB (Pb-Free)	50 Units / Rail
NTSB30100CT-1G	I <sup>2</sup> PAK (Pb-Free)	50 Units / Rail
NTSJ30100CTG	TO-220FP (Halide-Free)	50 Units / Rail
NTSB30100CTG	D <sup>2</sup> PAK (Pb-Free)	50 Units / Rail
NTSB30100CTT4G	D <sup>2</sup> PAK (Pb-Free)	800 / Tape & Reel

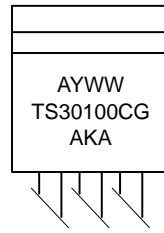
## MARKING DIAGRAMS



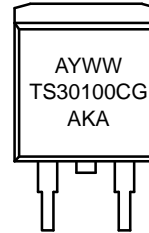
TO-220AB



TO-220FP



I<sup>2</sup>PAK

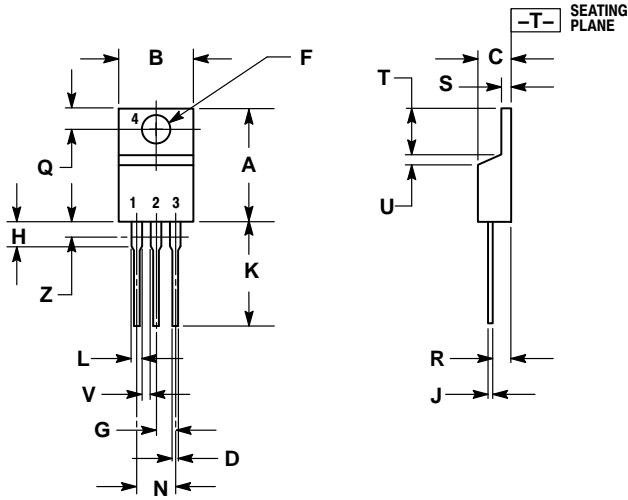


D<sup>2</sup>PAK

- A = Assembly Location
- Y = Year
- WW = Work Week
- AKA = Polarity Designator
- x = G or H
- G = Pb-Free Package
- H = Halide-Free Package

PACKAGE DIMENSIONS

TO-220  
CASE 221A-09  
ISSUE AH

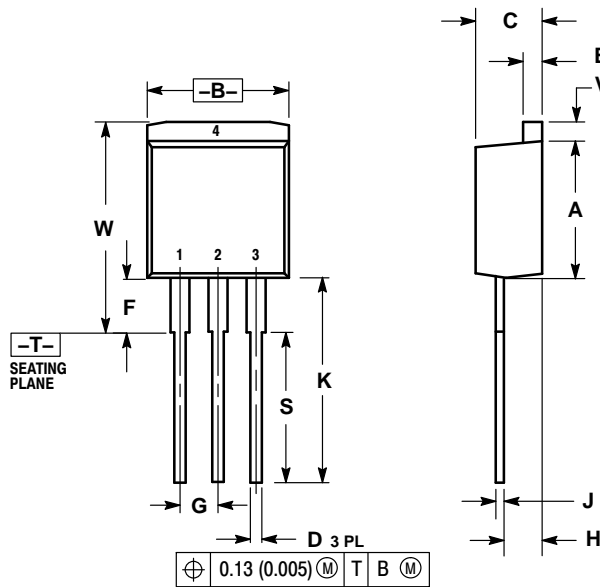


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

- STYLE 6:
1. ANODE
  2. CATHODE
  3. ANODE
  4. CATHODE

I<sup>2</sup>PAK (TO-262)  
CASE 418D  
ISSUE D

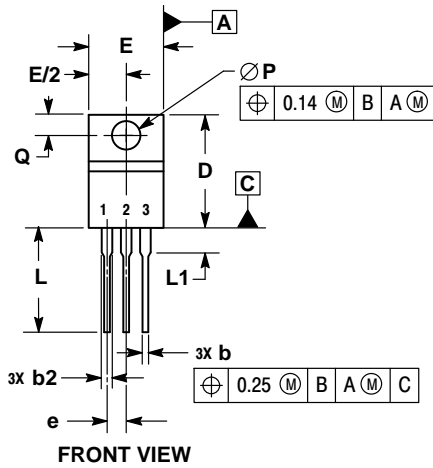


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

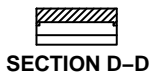
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.335	0.380	8.51	9.65
B	0.380	0.406	9.65	10.31
C	0.160	0.185	4.06	4.70
D	0.026	0.035	0.66	0.89
E	0.045	0.055	1.14	1.40
F	0.122 REF		3.10 REF	
G	0.100 BSC		2.54 BSC	
H	0.094	0.110	2.39	2.79
J	0.013	0.025	0.33	0.64
K	0.500	0.562	12.70	14.27
S	0.390 REF		9.90 REF	
V	0.045	0.070	1.14	1.78
W	0.522	0.551	13.25	14.00

PACKAGE DIMENSIONS

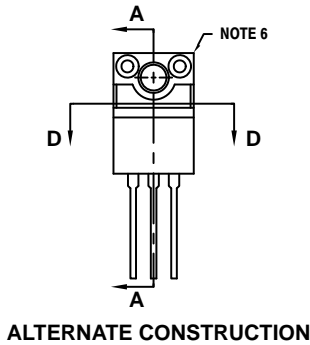
TO-220 FULLPACK, 3-LEAD  
CASE 221AH  
ISSUE F



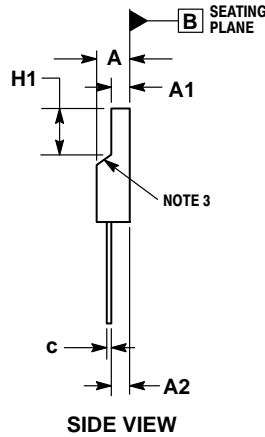
FRONT VIEW



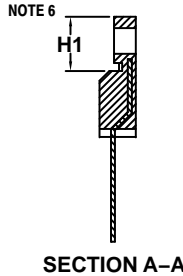
SECTION D-D



ALTERNATE CONSTRUCTION



SIDE VIEW



SECTION A-A

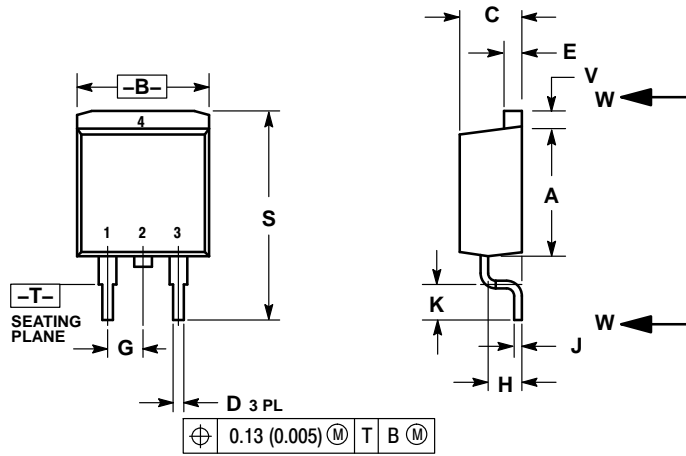
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
6. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOPE DEFINED BY DIMENSIONS A1 AND H1 FOR MANUFACTURING PURPOSES.

MILLIMETERS		
DIM	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.90
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.70	15.30
E	9.70	10.30
e	2.54 BSC	
H1	6.60	7.10
L	12.50	14.73
L1	---	2.80
P	3.00	3.40
Q	2.80	3.20

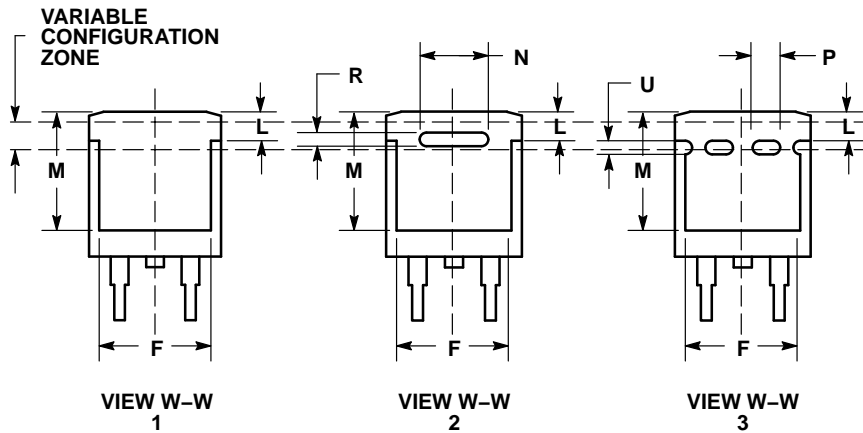
PACKAGE DIMENSIONS

D<sup>2</sup>PAK 3  
CASE 418B-04  
ISSUE K



- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: INCH.  
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40



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